

KSD526

Power Amplifier Applications

- Complement to KSB596



TO-220
1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|--|------------|------------------|
| V_{CBO} | Collector-Base Voltage | 80 | V |
| V_{CEO} | Collector-Emitter Voltage | 80 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current | 4 | A |
| I_B | Base Current | 0.4 | A |
| P_C | Collector Dissipation ($T_C=25^\circ\text{C}$) | 30 | W |
| T_J | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | - 55 ~ 150 | $^\circ\text{C}$ |

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|------------------------|--------------------------------------|---|----------|------|------|---------------|
| I_{CBO} | Collector Cut-off Current | $V_{CB} = 80\text{V}, I_E = 0$ | | | 30 | μA |
| I_{EBO} | Emitter Cut-off Current | $V_{EB} = 5\text{V}, I_C = 0$ | | | 100 | μA |
| BV_{CEO} | Collector-Emitter Breakdown Voltage | $I_C = 50\text{mA}, I_B = 0$ | 80 | | | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_E = 10\text{mA}, I_C = 0$ | 5 | | | V |
| h_{FE1} h_{FE2} | DC Current Gain | $V_{CE} = 50\text{V}, I_C = 0.5\text{A}$ $V_{CE} = 5\text{V}, I_C = 3\text{A}$ | 40 15 | 50 | 240 | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 3\text{A}, I_B = 0.3\text{A}$ | | 0.45 | 1.5 | V |
| $V_{BE(on)}$ | Base-Emitter ON Voltage | $V_{CE} = 5\text{V}, I_C = 3\text{A}$ | | 1 | 1.5 | V |
| f_T | Current Gain Bandwidth Product | $V_{CE} = 5\text{V}, I_C = 0.5\text{A}$ | 3 | 8 | | MHz |
| C_{ob} | Collector Output Capacitance | $V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$ | | 90 | | pF |

h_{FE} Classification

| Classification | R | O | Y |
|----------------|---------|----------|-----------|
| h_{FE} | 40 ~ 80 | 70 ~ 140 | 120 ~ 240 |

Typical Characteristics

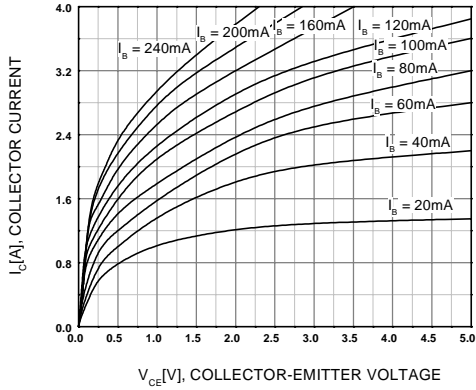


Figure 1. Static Characteristic

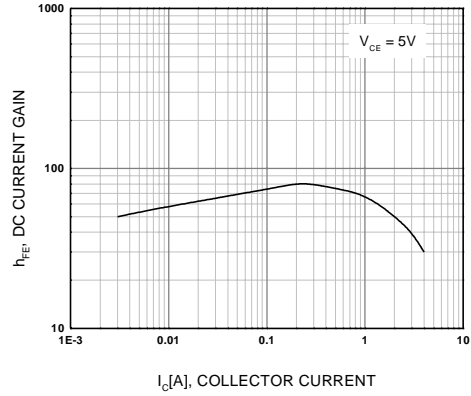


Figure 2. DC current Gain

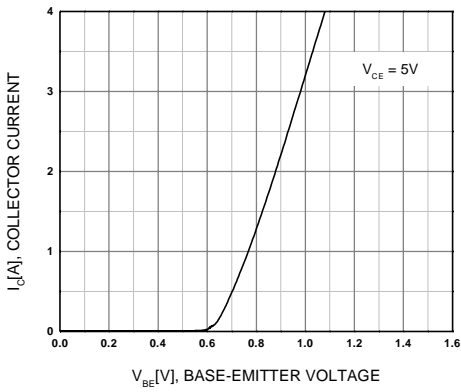


Figure 3. Base-Emitter On Voltage

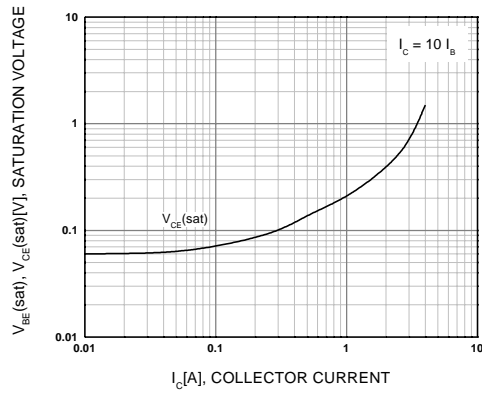


Figure 4. Collector-Emitter Saturation Voltage

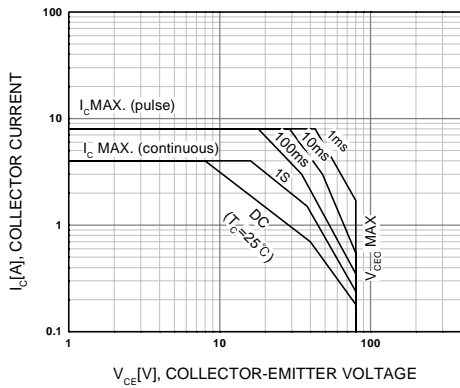


Figure 5. Safe Operating Area

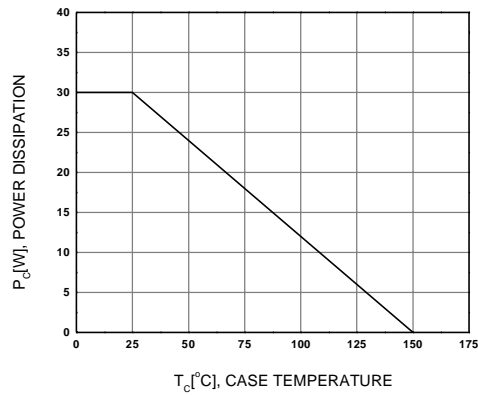
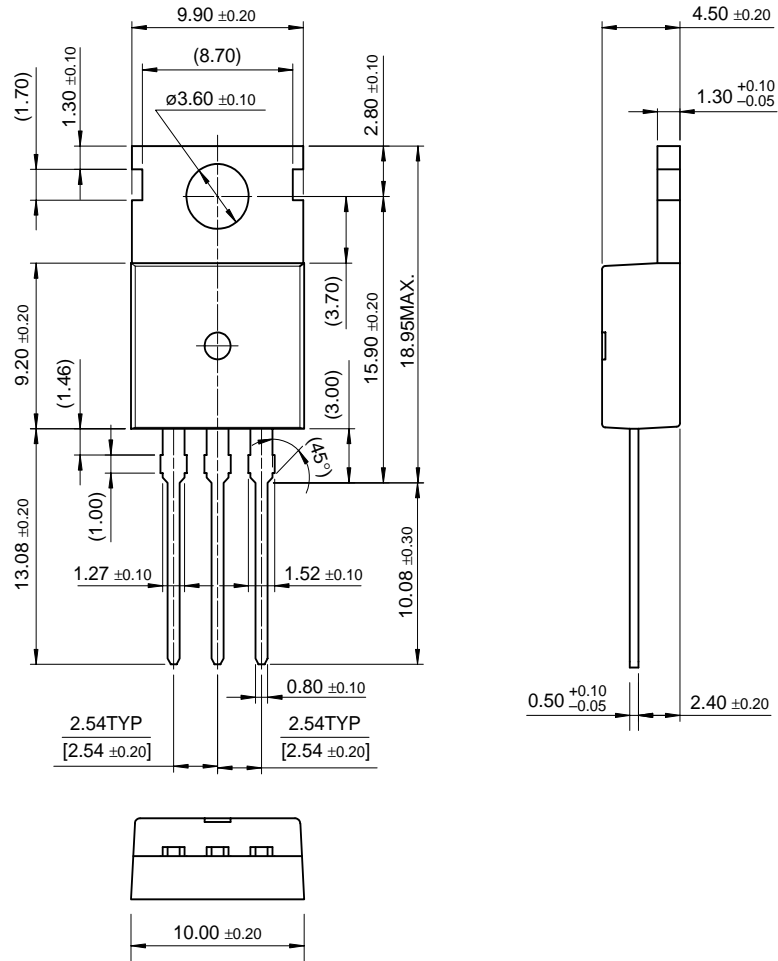


Figure 6. Power Derating

Package Dimensions

KSD526

TO-220



Dimensions in Millimeters

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| CROSSVOLT™ | POP™ | UHC™ |
| E ² CMOS™ | PowerTrench® | VCX™ |
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| FACT Quiet Series™ | QS™ | |
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| GTO™ | SuperSOT™-6 | |

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